

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/512,022	10/19/2004	Tetsuhiro Iida	93120	2202	
24628 7	590 08/04/2006		EXAMINER		
WELSH & KATZ, LTD			HITESHEW, FELISA CARLA		
120 S RIVERS	IDE PLAZA				
22ND FLOOR			ART UNIT	PAPER NUMBER	
CHICAGO, II	. 60606		1722		
			DATE MAILED: 08/04/2006	DATE MAILED: 08/04/2006	

Please find below and/or attached an Office communication concerning this application or proceeding.

				('			
		Application No.	Applicant(s)				
Office Action Summary		10/512,022	IIDA ET AL.				
		Examiner	Art Unit				
		Felisa C. Hiteshew	1722				
Period fo	The MAILING DATE of this communication ap or Reply	pears on the cover sheet with	the correspondence add	ress			
WHIC - Exte after - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REPL CHEVER IS LONGER, FROM THE MAILING D nsions of time may be available under the provisions of 37 CFR 1.1 SIX (6) MONTHS from the mailing date of this communication. O period for reply is specified above, the maximum statutory period are to reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailing ed patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNICA 136(a). In no event, however, may a reply will apply and will expire SIX (6) MONTHS e, cause the application to become ABANI	TION. be timely filed from the mailing date of this condoned (35 U.S.C. § 133).				
Status		/					
1) 🗌	Responsive to communication(s) filed on	/					
2a) <u></u>	This action is FINAL . 2b) ☐ This action is non-final.						
3) 🗌	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
	closed in accordance with the practice under	Ex parte Quayle, 1935 C.D. 1	1, 453 O.G. 213.	•			
Disposit	ion of Claims						
4)⊠	Claim(s) <u>1-16</u> is/are pending in the application	٦.					
	4a) Of the above claim(s) is/are withdrawn from consideration.						
5)⊠	Claim(s) 2 and 4-10 is/are allowed.						
6)⊠	6)⊠ Claim(s) <u>1,3,11-14 and 16</u> is/are rejected.						
•	Claim(s) <u>15</u> is/are objected to.						
8)	Claim(s) are subject to restriction and/o	or election requirement.					
Applicat	ion Papers						
9) 🗌	The specification is objected to by the Examine	er.					
10)	The drawing(s) filed on is/are: a) acc	cepted or b) objected to by	the Examiner.				
	Applicant may not request that any objection to the						
🗀	Replacement drawing sheet(s) including the correct						
11)	The oath or declaration is objected to by the E	examiner. Note the attached C	Trice Action or form PT	J-152.			
Priority (under 35 U.S.C. § 119						
	Acknowledgment is made of a claim for foreign All b) Some * c) None of:		19(a)-(d) or (f).				
	1. Certified copies of the priority documen		r e Al.				
	2. Certified copies of the priority documen	• • •		Stago			
	 Copies of the certified copies of the price application from the International Burea 	•	ceived in this ivational c	Stage			
* 9	See the attached detailed Office action for a lis		ceived.				
·							
Attachmer	nt(s)						
	ce of References Cited (PTO-892)	4) Interview Sum	nmary (PTO-413) fail Date				
3) 🔯 Infor	ce of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08 er No(s)/Mail Date <u>see attahced paper</u> .		mal Patent Application (PTO	-152)			

Application/Control Number: 10/512,022 Page 2

Art Unit: 1722

Priority

1. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Information Disclosure Statement

The PTOL 1449 has been received, reviewed and considered.

Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. The factual inquiries set forth in *Graham* v. *John Deere Co.*, 383 U.S. 1, 148 USPQ 459 (1966), that are applied for establishing a background for determining obviousness under 35 U.S.C. 103(a) are summarized as follows:
 - 1. Determining the scope and contents of the prior art.
 - 2. Ascertaining the differences between the prior art and the claims at issue.
 - 3. Resolving the level of ordinary skill in the pertinent art.
 - 4. Considering objective evidence present in the application indicating obviousness or nonobviousness.
- 4. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to

Application/Control Number: 10/512,022

Art Unit: 1722

consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

Claims 1,3,11-14 and 16 are rejected under 35 U.S.C. 103(a) as being 5. unpatentable over Japanese Abstract 09-165298 in view of Japanese Abstract 57-017494.

Japanese Abstract 09-165298 teaches a magnetic Czochralski (MCZ) process for pulling up a silicon single crystal with a 2.0mm diameter having >1500 gauss. The magnetic field is gradually decreased and the strength of the magnetic field is decreased to 0 it moves from the shoulder-making step to a drum-making step. A dislocation-free single silicon crystal having an <110> crystal axis is produced.

The difference being that Japanese Abstract 09-165298 does not teach a <110> orientation with an incline.

Japanese Abstract 57-017494 teaches a Czochralski method for pulling a single crystal having uniform purity. The pulling direction of the crystal is inclined by 5W10* from a low index orientation, <111>, <100> or <110> of the crystal. Japanese Abstract 57-017494 also teaches cutting or "slicing" a wafer out from a part with solidification. It would have been obvious to one of ordinary skill in the art to modify and optimize the process parameter limitations as well as the product, as taught by, Japanese Abstract 09-165298 with the process parameter limitations as well as the product, as taught by, Japanese Abstract 57-017494. The motivation being that a high quality dislocationfree single silicon crystal can be pulled up having a <110> crystal axis with uniformity.

A reference is good not only for what it teaches by direct anticipation but also for

Application/Control Number: 10/512,022 Page 4

Art Unit: 1722

what one of ordinary skill might reasonably infer from the teachings. In re Opprect 12 USPQ 2d 1235, 1236 (CAFC 1989); In re Bode 193 USPQ 12; In re Lamberti 192 USPQ 278; In re Bozek 163 USPQ 545, 549 (CCPA 1969); In re Van Mater 144 USPQ 421; In re Jacoby 135 USPQ 317; In re LeGrice 133 USPQ 365; In re Preda 159 USPQ 342 (CCPA 1968).

Allowable Subject Matter

- 6. Claim2 and 4-10 are allowed.
- 7. As allowable subject matter has been indicated, applicant's reply must either comply with all formal requirements or specifically traverse each requirement not complied with. See 37 CFR 1.111(b) and MPEP § 707.07(a).
- 8. Claim 15 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

A method for producing single crystal silicon by which the single crystal silicon is produced by dipping a seed crystal in a melt and pulling the seed crystal up along an axial direction thereof, comprising:

a step of preparing the seed crystal in which a <110> crystal orientation is inclined at a predetermined angle θ with respect to the axial direction;

a dislocation network elimination step of gradually reducing a diameter-of the single crystal silicon to d1 after the seed crystal has been brought into contact with the melt; and

a slip dislocation elimination step of further growing the single crystal silicon by a length of at least d1/tan θ , while maintaining the diameter thereof at almost d1.

FELISA HITESHEW PRIMARY EXAMINER

A41728